

新品发布

OMG!!!
泰酷啦!

N100V MOSFET：给PD电源安排“低耗抗造”超顶内核~

产品特点

- 1.采用最新优化的SGT工艺, 产品内阻低, 开关特性优异;
- 2.采用PDFN5*6-8L 封装, 适用于PD电源同步整流应用;
- 3.针对电源应用的各种工作状态, 优化MOS产品EAS能力, 提高产品的可靠性。

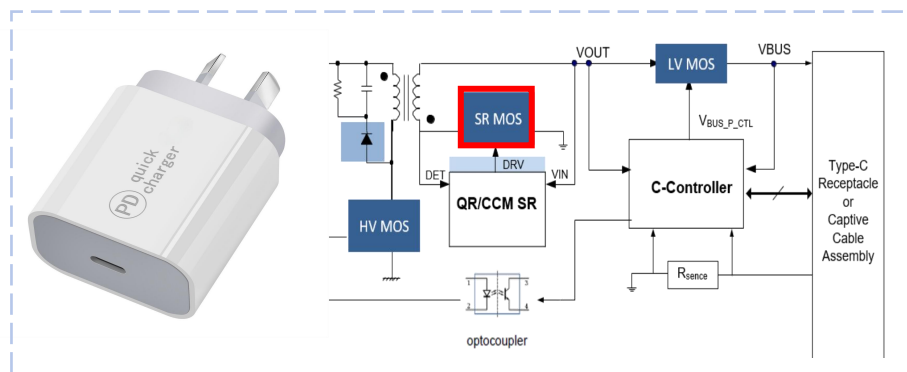
更多产品详见官网

Product Name	Package	Vds (V)	ID (A)	Vth (V) typ.	Rds10V (mohm) typ.	Rds10V (mohm) max.	Qg10V (nC) typ.	Tj (°C)	N/P
YJG8D0G10H	PDFN5060-8L	100	83	3	6.3	8	22.7	-55-150	N
YJG7D4G10H	PDFN5060-8L	100	86	3	6.1	7.4	23.4	-55-150	N
YJG6D3G10H	PDFN5060-8L	100	100	3	5.1	6.3	26.3	-55-150	N
YJG5D2G10H	PDFN5060-8L	100	105	3	4.3	5.2	35.8	-55-150	N
YJG4D6G10H	PDFN5060-8L	100	149	3	3.7	4.6	40.2	-55-150	N

产品介绍

扬杰科技最新推出了一系列用于PD电源的N100V MOSFET产品, 产品采用特殊优化的SGT技术, 具有较低的导通电阻Rdson和栅极电荷Qg, 明显降低导通和开关损耗, 同时提升了MOSFET抗雪崩冲击能力。

新品发布



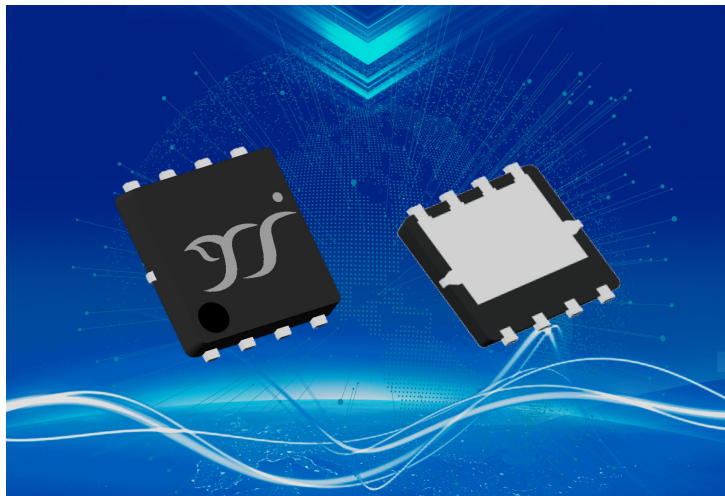
PD充电器

典型应用

NEW
PRODUCT

New N100V MOSFET for PD Power Supply

Product
Features



Product Introduction

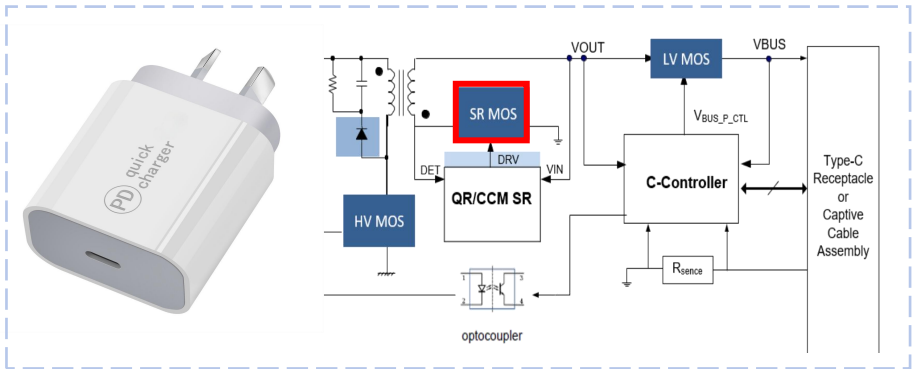
YangJie technology recently launched a series of N100V mosfet products for PD power supplies. The products adopt specially optimized SGT technology, with low $R_{ds(on)}$ and Q_g , significantly reducing forward voltage drop and switching losses, while enhancing the avalanche resistance of the mosfet.

新品发布

- 1. The product utilizes optimized SGT technology, featuring low on-resistance and excellent switching performance.
- 2. The product adopts PDFN5*6-8L package, suitable for PD power synchronous rectifier applications
- 3. For various working states of power supply applications, optimize the EAS capability of MOS products to enhance their reliability.

Please refer to the official website for more products

Product Name	Package	Vds (V)	ID (A)	Vth (V) typ.	Rds10V (mohm) typ.	Rds10V (mohm) max.	Qg10V (nC) typ.	Tj (°C)	N/P
YJG8D0G10H	PDFN5060-8L	100	83	3	6.3	8	22.7	-55-150	N
YJG7D4G10H	PDFN5060-8L	100	86	3	6.1	7.4	23.4	-55-150	N
YJG6D3G10H	PDFN5060-8L	100	100	3	5.1	6.3	26.3	-55-150	N
YJG5D2G10H	PDFN5060-8L	100	105	3	4.3	5.2	35.8	-55-150	N
YJG4D6G10H	PDFN5060-8L	100	149	3	3.7	4.6	40.2	-55-150	N



Power Delivery charger

Typical
Applica-
-tions